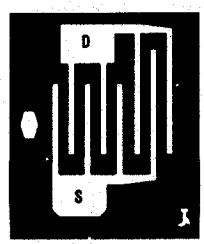
P-CHANNEL JUNCTION FET

Solitron Devices, Inc.

CHIP NUMBER

FP5.3



Die Size: .15 x 20 (mils)
0.381 x 0.508(mm)
Pad Size: 3 x 4 (mils)
0.076 x 0.102(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000 Å Aluminum

Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

a) the die be eutectically mounted with gold silicon preform 98/2%.

b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

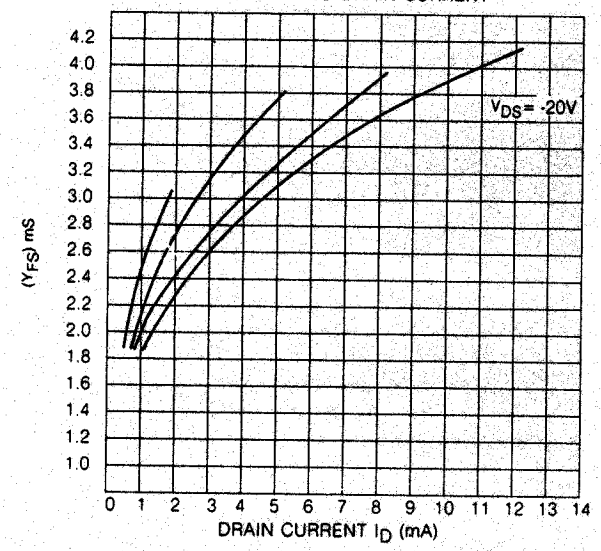
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BV_{GSS}	30	40	50	V	V_{DS} = —0, I_G = 1μA
I_{DSS}	0.5	8.0	20	mA	V_{DS} = —20V, V_{GS} = 0
g_{fs}		4000		μmho	V_{DS} = —20V, V_{GS}, = 0
I_{GSS}		30	200	pA	V_{GS} = —20V, V_{DS} = 0
r_{DS}		300		Ω	V_{DS} = 100mV, V_{GS} = 0
$V_{GS(off)}$	1.0	2.5	8.0	V	V_{DS} = —20V, I_D = 1nA
C_{rss}		1.8	2.5	pF	V_{DS} = —20V, V_{GS} = 0, f = 1MHz
C_{iss}		7.0	9.0	pF	V_{DS} = —20V, V_{GS} = 0, f = 1MHz

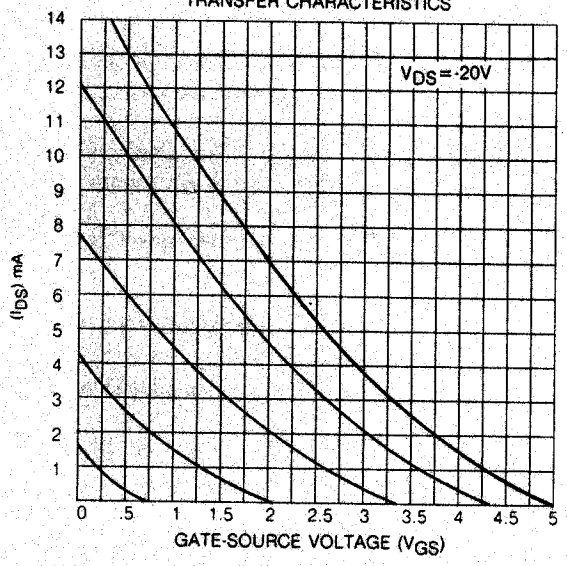
TYPICAL DEVICE TYPES: UC400, UC410, UC420, 2N2607, 2N2608, 2N2609, 2N2842, 2N2844

CHIP TYPE FP5.3

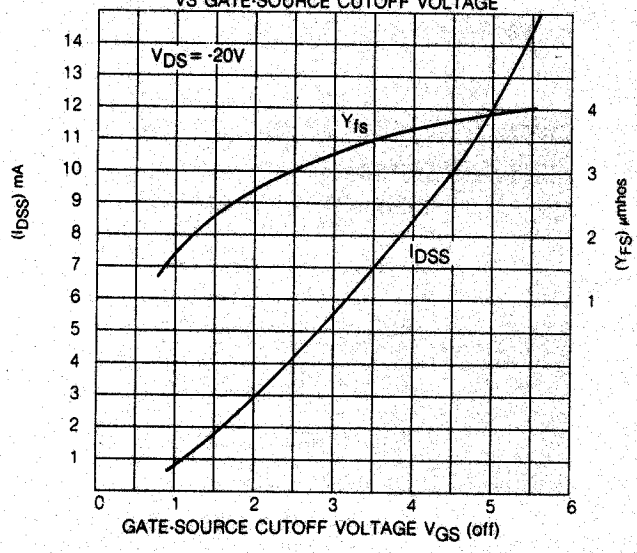
FORWARD TRANSADMITTANCE
VS OPERATING DRAIN CURRENT



TRANSFER CHARACTERISTICS



FORWARD TRANSADMITTANCE
VS GATE-SOURCE CUTOFF VOLTAGE



OUTPUT TRANSFER CHARACTERISTICS